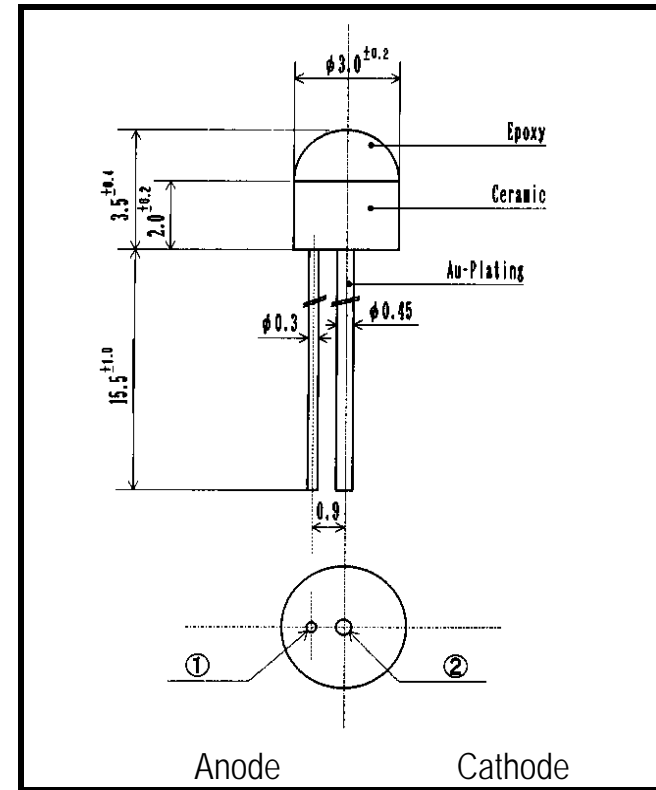


# PDC120M3B

# Photo Diode



- FEATURES**
- High Reliability
  - Very Small Dark Current
  - Linearity of L vs I<sub>sc</sub>
  - Compact
- APPLICATIONS**
- Optical Switches
  - Optical Sensors
  - Optical Detectors

## 1. ABSOLUTE MAXIMUM RATINGS (Ta=25 °C)

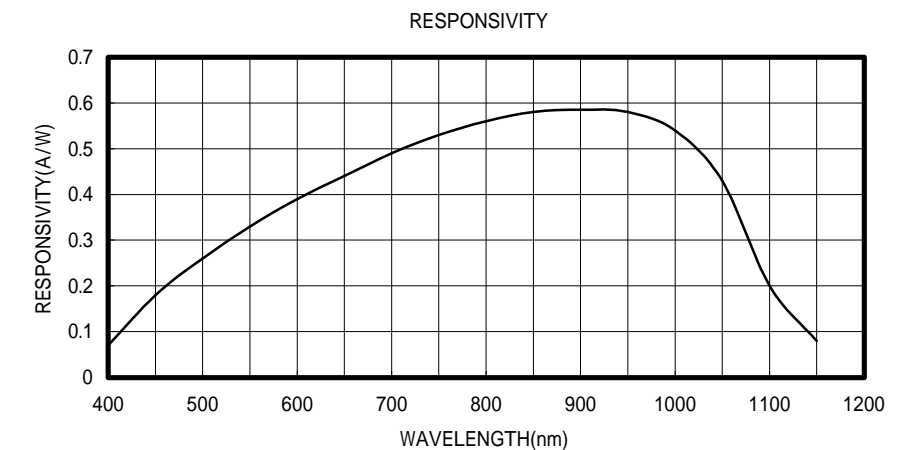
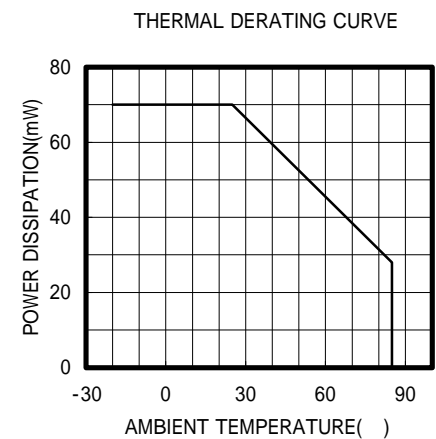
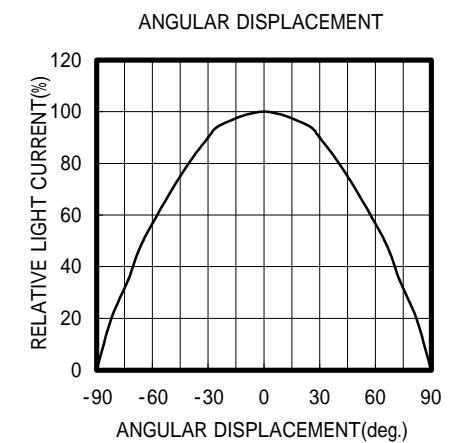
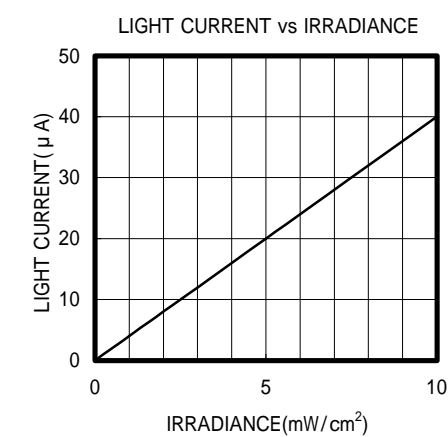
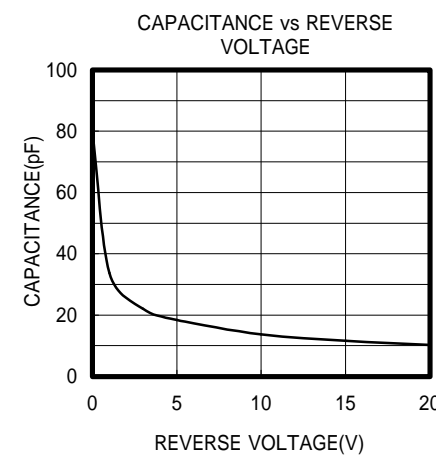
ITEM	SYMBOL	RATINGS	UNIT
Reverse Voltage	VR	20	V
Power Dissipation	PD	70	mW
Operating Temp.	Topr	-20 TO 85	
Storage Temp.	Tstg	-30 TO 100	
Junction Temp.	Tj	100	
Lead Soldering Temp.*1	Tls	260	

\*1:Time 5 Sec max,Position:Up to 3mm from the body

## 2. ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25 °C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Open Circuit Voltage	Voc	Ee=5mW/cm <sup>2</sup>		0.35		V
Light Current	IL	VR=10V, Ee=5mW/cm <sup>2</sup>		20		μA
Dark Current	ID	VR=10V		0.5	5	nA
Curve Factor	CF	Ee=5mW/cm <sup>2</sup>	0.55			-
Spectral Sensitivity				400 ~ 1100		nm
Peak Sensitivity Wave Length	p			950		nm
Angular Response				±65		deg
Switching time (Rise Time)	Tr	RL=50 , Vr=0V			2	μS
Switching time (Fall Time)	Tf	RL=50 , Vr=0V			2	μS
Junction Capacitance	Cj	at 1MHz V=0V		80	100	pF

Color temperature=2870°K Standard Tungsten Lump



OPTRANS

2-6-11 MASUKATA, TAMA-KU, KAWASAKI 214-0032, JAPAN  
 TEL.81(44)932-6491 / FAX.81(44)932-8281  
 E-mail: oprans@mb.kcom.ne.jp